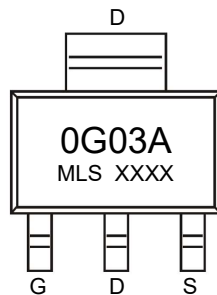


Features

- Trench Power LV MOSFET technology
- High Density Cell Design for Low $R_{DS(ON)}$
- High Speed switching

Application

- CoBattery protection
- Load switch
- Power management

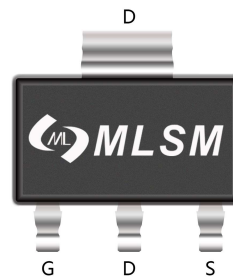


0G03A : Device code
 XXXX : Code

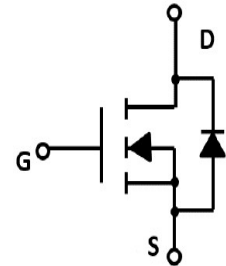
Marking and pin assignment

Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
60V	160mΩ@10V	3A
	250mΩ@4.5V	



SOT-223 top view



Schematic diagram



Pb-Free



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V_{DS}	Drain-Source Breakdown Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-50 to 155	°C
I_S	Diode Continuous Forward Current	$T_c=25^\circ\text{C}$ 3	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_c=25^\circ\text{C}$ 10	A
I_D	Continuous Drain Current	$T_c=25^\circ\text{C}$ 3	A
P_D	Maximum Power Dissipation	$T_c=25^\circ\text{C}$ 1.66	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	125	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MT0G03A	SOT-223	0G03A	2,500	5,000	35,000	13"reel

Electrical Characteristics (TJ=25°C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV(BR)DSS	Drain-Source Breakdown Voltage	VGS=0V, ID=250μA	60	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=60V, VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V, VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=250μA	1.0	1.5	2.5	V
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=3A	--	130	160	mΩ
		VGS=4.5V, ID=2A	--	150	250	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
CISS	Input Capacitance	VDS=20V, VGS=0V, f=1MHz	--	245	--	pF
COSS	Output Capacitance		--	30	--	pF
CRSS	Reverse Transfer Capacitance		--	20	--	pF
Switching Characteristics						
Qg	Total Gate Charge	VDS=10V, ID=3A, VGS=24V	--	5.5	--	nC
Qgs	Gate Source Charge		--	1.3	--	nC
Qgd	Gate Drain Charge		--	1	--	nC
td(on)	Turn-on Delay Time	VDS=24V, ID=3A, VGS=10V, RG=3Ω	--	4.2	--	nS
tr	Turn-on Rise Time		--	18.5	--	nS
td(off)	Turn-Off Delay Time		--	8	--	nS
tf	Turn-Off Fall Time		--	19	--	nS
Source- Drain Diode Characteristics						
VSD	Forward on voltage	TJ=25°C, IS=3A	--	--	1.2	V

Typical Operating Characteristics

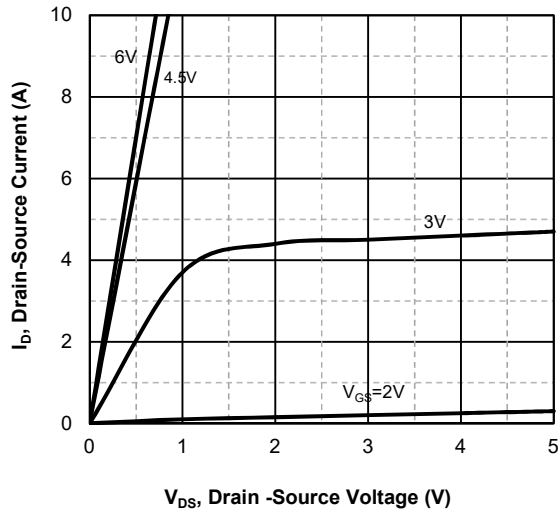


Fig1. Typical Output Characteristics

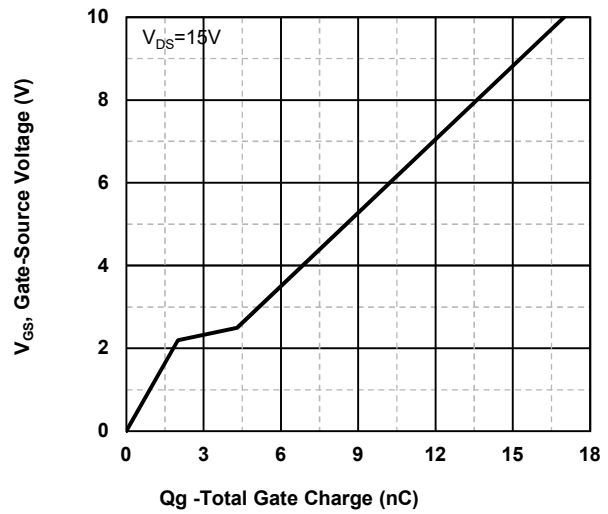


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

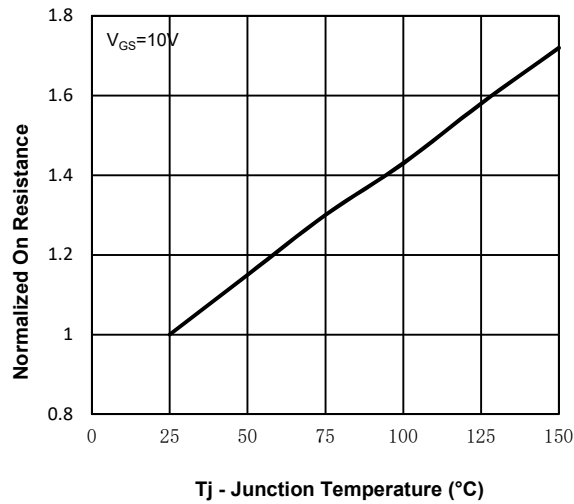


Fig3. Normalized On-Resistance Vs. Temperature

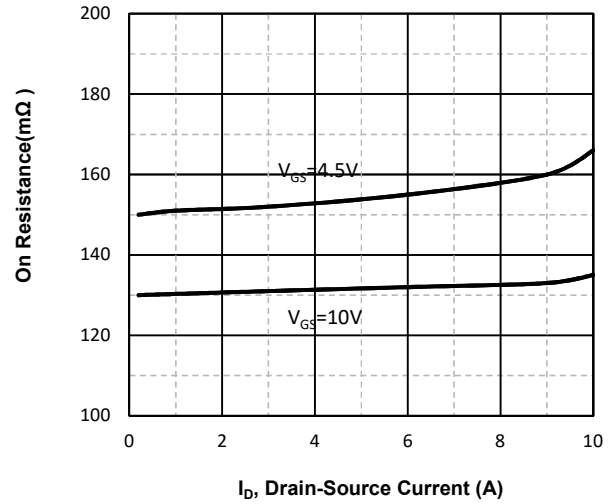


Fig4. On-Resistance Vs. Drain-Source Current

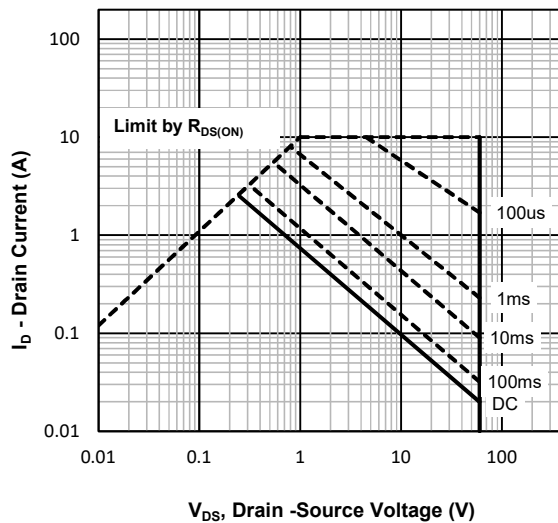


Fig5. Maximum Safe Operating Area

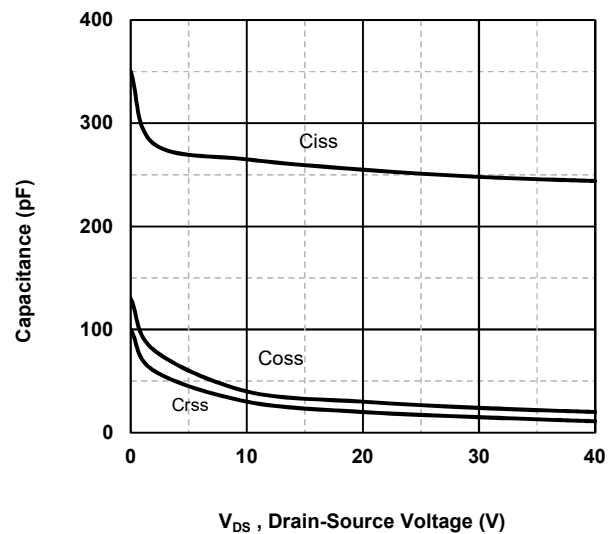
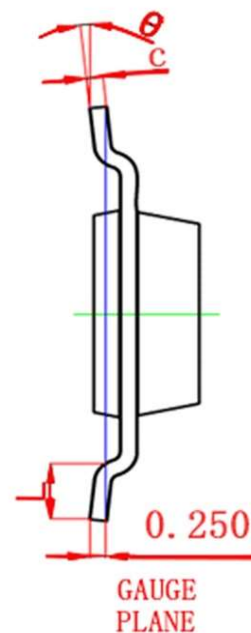
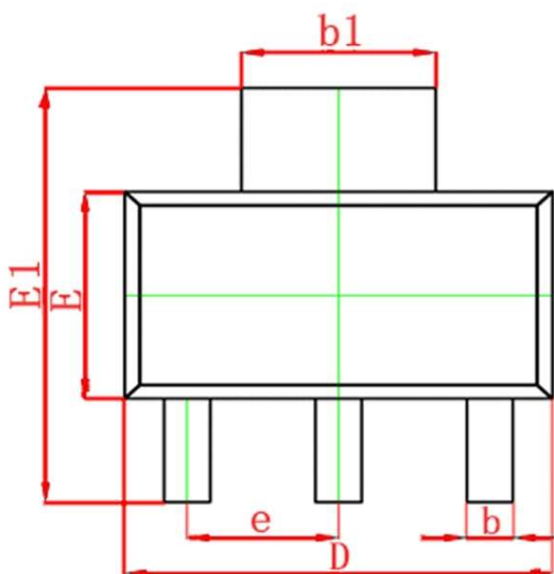


Fig6 Typical Capacitance Vs. Drain-Source Voltage

SOT-223 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	--	1.800	--	0.071
A1	0.020	0.100	0.001	0.004
A2	1.500	1.700	0.059	0.067
b	0.660	0.840	0.026	0.033
b1	2.900	3.100	0.114	0.122
c	0.230	0.350	0.009	0.014
D	6.300	6.700	0.248	0.264
E	3.300	3.700	0.130	0.146
E1	6.700	7.300	0.264	0.287
e	2.300(BSC)		0.091(BSC)	
L	0.750	--	0.030	--
θ	0°	10°	0°	10°